

DS90C032QML

LVDS Quad CMOS Differential Line Receiver

General Description

The DS90C032 is a quad CMOS differential line receiver designed for applications requiring ultra low power dissipation and high data rates.

The DS90C032 accepts low voltage differential input signals and translates them to CMOS (TTL compatible) output levels. The receiver supports a TRI-STATE® function that may be used to multiplex outputs.

The DS90C032 and companion line driver (DS90C031) provide a new alternative to high power psuedo-ECL devices for high speed point-to-point interface applications.

In addition, the DS90C032A provides power-off high impedance LVDS inputs. This feature assures minimal loading effect on the LVDS bus lines when V_{CC} is not present.

Features

- High impedance LVDS inputs with power-off.
- Accepts small swing (330 mV) differential signal levels
- Low power dissipation.
- Low differential skew.
- Low chip to chip skew.
- Pin compatible with DS26C32A
- Compatible with IEEE 1596.3 SCI LVDS standard

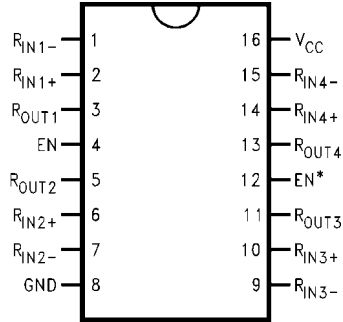
Ordering Information

NS Part Number	SMD Part Number	NS Package Number	Package Description
DS90C032E-QML	5962-9583401Q2A	E20A	20LD Leadless Chip Carrier
DS90C032W-QML	5962-9583401QFA	W16A	16LD Ceramic Flatpack
DS90C032WG-QML	5962-9583401QZA	WG16A	16LD Ceramic SOIC
DS90C032W-QMLV	5962-9583401VFA	W16A	16LD Ceramic Flatpack
DS90C032WG-QMLV	5962-9583401VZA	WG16A	16LD Ceramic SOIC
DS90C032WLQMLV	5962L9583401VFA 50K rd(Si)	W16A	16LD Ceramic Flatpack
DS90C032WGLQMLV	5962L9583401VZA 50K rd(Si)	WG16A	16LD Ceramic SOIC

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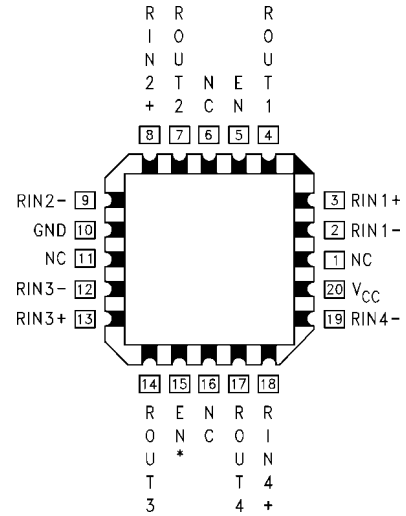
Connection Diagrams

Dual-In-Line Pictured



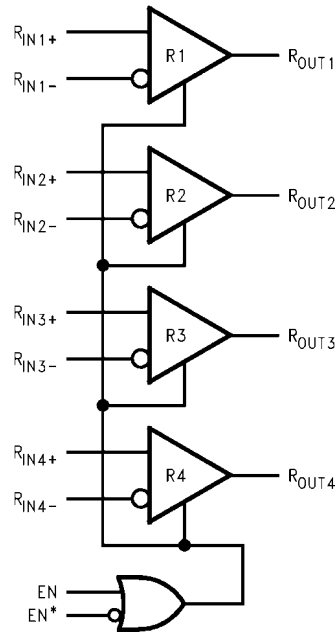
20163701
See NS Package Number W16A & WG16A

Leadless Chip Carrier Package



20163720
See NS Package Number E20A

Functional Diagram and Truth Tables



20163702

Receiver

ENABLES		INPUTS	OUTPUT
EN	EN*	R _{I+} - R _{I-}	R _O
L	H	X	Z
All other combinations of ENABLE inputs		V _{ID} ≥ 0.1V	H
		V _{ID} ≤ -0.1V	L

Absolute Maximum Ratings (Note 1)

Supply Voltage (V_{CC})	-0.3V to +6V
Input Voltage (R_{I+} , R_{I-})	-0.3V to ($V_{CC} + 0.3V$)
Enable Input Voltage (EN , EN^*)	-0.3V to ($V_{CC} + 0.3V$)
Output Voltage (R_O)	-0.3V to ($V_{CC} + 0.3V$)
Storage Temperature Range (T_{Stg})	$-65^{\circ}C \leq T_A \leq +150^{\circ}C$
Lead Temperature Range Soldering (4 sec.)	+260°C
Maximum Package Power Dissipation @ +25°C (Note 2)	
LCC Package	1,830 mW
Ceramic Flatpack	1,400 mW
Ceramic SOIC	1,400 mW
Thermal Resistance	
θ_{JA}	
LCC Package	82°C/W
Ceramic Flatpack	145°C/W
Ceramic SOIC	145°C/W
θ_{JC}	
LCC Package	20°C/W
Ceramic Flatpack	20°C/W
Ceramic SOIC	20°C/W
ESD Rating (Note 3)	2KV

Recommended Operating Conditions

	Min	Typ	Max
Supply Voltage (V_{CC})	+4.5V	+5.0V	+5.5V
Receiver Input Voltage	Gnd		2.4V
Operating Free Air Temperature (T_A)	-55°C	+25°C	+125°C

Radiation Features

DS90C032WLQMLV	50 krad (Si)
DS90C032WGLQMLV	50 krad (Si)

Quality Conformance Inspection

Mil-Std-883, Method 5005 - Group A

Subgroup	Description	Temp °C
1	Static tests at	25
2	Static tests at	125
3	Static tests at	-55
4	Dynamic tests at	25
5	Dynamic tests at	125
6	Dynamic tests at	-55
7	Functional tests at	25
8A	Functional tests at	125
8B	Functional tests at	-55
9	Switching tests at	25
10	Switching tests at	125
11	Switching tests at	-55
12	Settling time at	25
13	Settling time at	125
14	Settling time at	-55

DC Parameters (Note 7)

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
V_{ThL}	Differential Input Low Threshold	$V_{CM} = +1.2V$	(Note 4)		-100	mV	1, 2, 3
V_{ThH}	Differential Input High Threshold	$V_{CM} = +1.2V$	(Note 4)		100	mV	1, 2, 3
I_{In}	Input Current (Input Pins)	$V_{CC}=5.5V, V_I = 2.4V$			± 10	μA	1, 2, 3
		$V_{CC} = 5.5V, V_I = 0$			± 10	μA	1, 2, 3
		$V_{CC} = 0.0V, V_I = 2.4V$			± 10	μA	1, 2, 3
		$V_{CC} = 0.0V, V_I = 0.0V$			± 10	μA	1, 2, 3
V_{OH}	Output High Voltage	$V_{CC} = 4.5V, I_{OH} = -0.4 mA,$ $V_{ID} = 200mV$		3.8		V	1, 2, 3
V_{OL}	Output Low Voltage	$V_{CC} = 4.5, I_{OL} = 2 mA,$ $V_{ID} = -200mV$			0.3	V	1, 2, 3
I_{OS}	Output Short Circuit Current	Enabled, $V_O = 0V$		-15	-100	mA	1, 2, 3
I_{OZ}	Output TRI-STATE Current	Disabled, $V_O = 0V$ or V_{CC}			± 10	μA	1, 2, 3
V_{IH}	Input High Voltage		(Note 4)	2.0		V	1, 2, 3
V_{IL}	Input Low Voltage		(Note 4)		0.8	V	1, 2, 3
I_I	Input Current (Enable Pins)	$V_{CC} = 5.5V$			± 10	μA	1, 2, 3
V_{CL}	Input Clamp Voltage	$I_{Cl} = -18mA$			-1.5	V	1, 2, 3
I_{CC}	No Load Supply Current	EN, EN* = V_{CC} or Gnd, Inputs Open			11	mA	1, 2, 3
		EN, EN* = 2.4 or 0.5, Inputs Open			11	mA	1, 2, 3
I_{CCZ}	No Load Supply Current Receivers Disabled	EN = Gnd, EN* = V_{CC} , Inputs Open			11	mA	1, 2, 3

AC Parameters (Note 7)

The following conditions apply, unless otherwise specified.

AC: $V_{CC} = 4.5V / 5.0V / 5.5V$, $C_L = 20pF$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
t_{PHLD}	Differential Propagation Delay High to Low	$V_{ID} = 200mV$, Input pulse = 1.1V to 1.3V, $V_I = 1.2V$ (0V differential) to $V_O = 1/2 V_{CC}$		1.0	8.0	ns	9, 10, 11
t_{PLHD}	Differential Propagation Delay Low to High	$V_{ID} = 200mV$, Input pulse = 1.1V to 1.3V, $V_I = 1.2V$ (0V differential) to $V_O = 1/2 V_{CC}$		1.0	8.0	ns	9, 10, 11
t_{SKD}	Differential Skew $ t_{PHLD} - t_{PLHD} $	$C_L = 20pF$, $V_{ID} = 200mV$			3.0	ns	9, 10, 11
t_{SK1}	Channel to Channel Skew	$C_L = 20pF$, $V_{ID} = 200mV$	(Note 5)		3.0	ns	9, 10, 11
t_{SK2}	Chip to Chip Skew	$C_L = 20pF$, $V_{ID} = 200mV$	(Note 6)		7.0	ns	9, 10, 11
t_{PLZ}	Disable Time Low to Z	Input pulse = 0V to 3.0V, $V_O = V_{OL} + 0.5V$, $R_L = 1K\Omega$ to V_{CC} , $V_I = 1.5V$			20	ns	9, 10, 11
t_{PHZ}	Disable Time High to Z	Input pulse = 0V to 3.0V, $V_I = 1.5V$, $V_O = V_{OH} - 0.5V$, $R_L = 1K\Omega$ to Gnd			20	ns	9, 10, 11
t_{PZH}	Enable Time Z to High	Input pulse = 0V to 3.0V, $V_I = 1.5V$, $V_O = 50\%$, $R_L = 1K\Omega$ to Gnd			20	ns	9, 10, 11
t_{PZL}	Enable Time Z to Low	Input pulse = 0V to 3.0V, $V_I = 1.5V$, $V_O = 50\%$, $R_L = 1K\Omega$ to V_{CC}			20	ns	9, 10, 11

AC/DC Post Radiation Limits (Note 7)

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-groups
I_{CC}	No Load Supply Current	EN, EN* = V_{CC} or Gnd, Inputs Open			20	mA	1
		EN, EN* = 2.4 or 0.5, Inputs Open			20	mA	1
I_{CCZ}	No Load Supply Current Receivers Disabled	EN = Gnd, EN* = V_{CC} , Inputs Open			20	mA	1

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 2: Derate LCC @ 12.2mW/°C above +25°C. Derate ceramic flatpack @ 6.8mW/°C above +25°C

Note 3: Human body model, 1.5 kΩ in series with 100 pF.

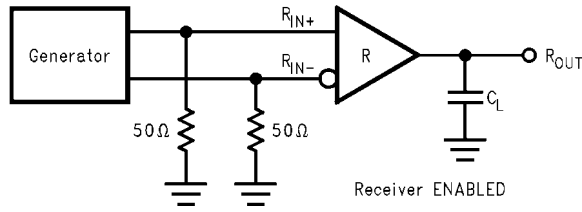
Note 4: Tested during V_{OH} / V_{OL} tests.

Note 5: Channel-to-Channel Skew is defined as the difference between the propagation delay of one channel and that of the others on the same chip with an event on the inputs.

Note 6: Chip to Chip Skew is defined as the difference between the minimum and maximum specified differential propagation delays.

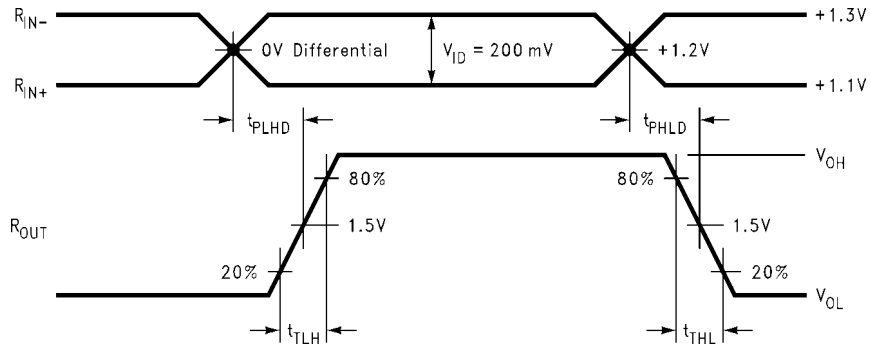
Note 7: Pre and post irradiation limits are identical to those listed under AC & DC electrical characteristics except as listed in the "Post Radiation Limits" table. Radiation end point limits for the noted parameters are guaranteed only for the conditions, as specified.

Parameter Measurement Information



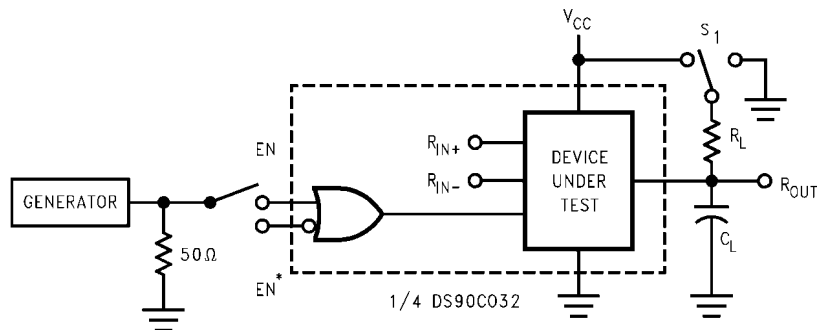
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FIGURE 1. Receiver Propagation Delay and Transition Time Test Circuit



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FIGURE 2. Receiver Propagation Delay and Transition Time Waveforms



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C_L includes load and test jig capacitance.
 $S_1 = V_{CC}$ for t_{PZL} and t_{PLZ} measurements.
 $S_1 = Gnd$ for t_{PZH} and t_{PHZ} measurements.

FIGURE 3. Receiver TRI-STATE Delay Test Circuit

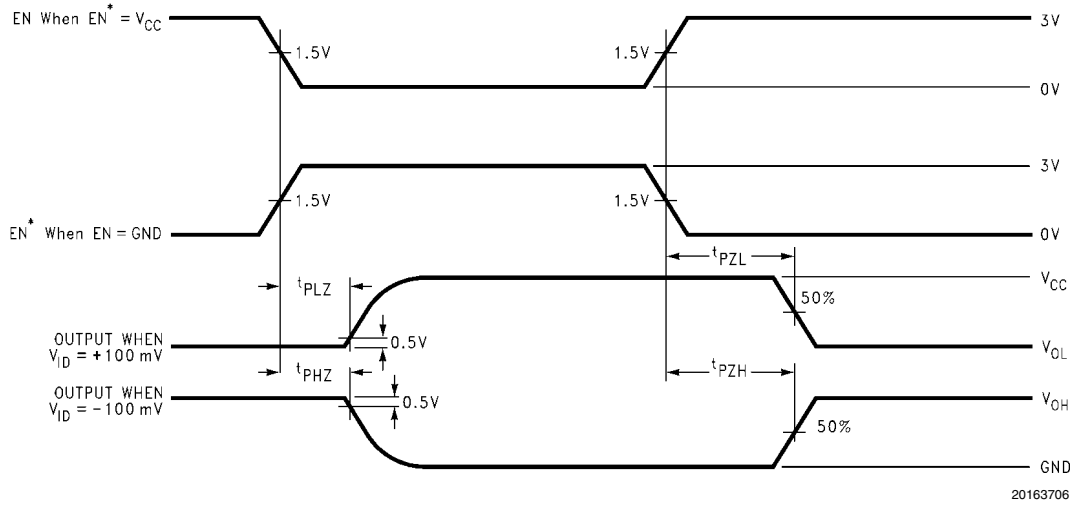
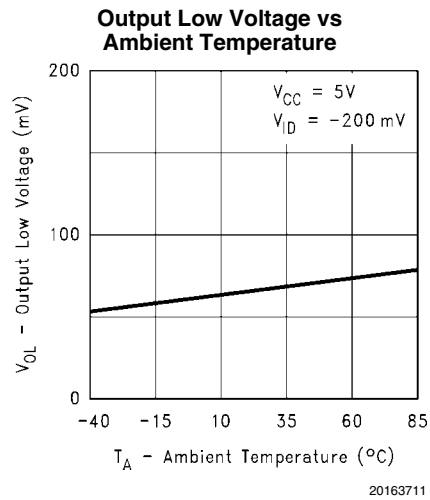
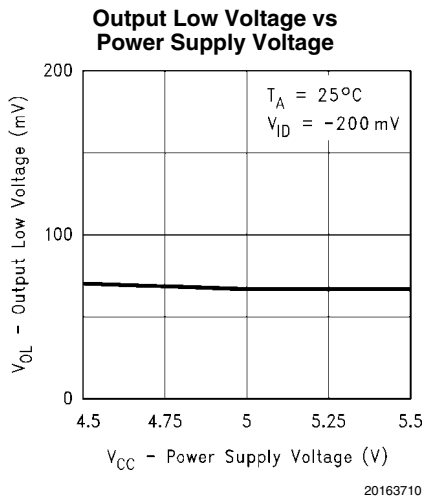
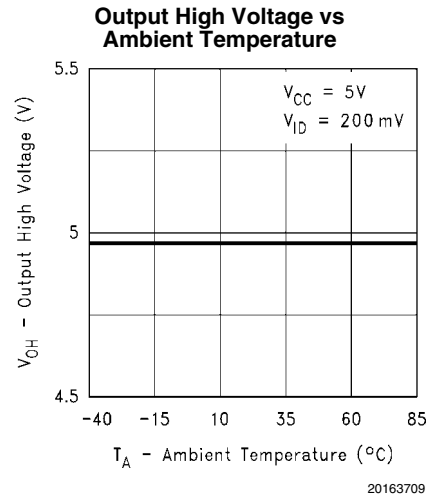
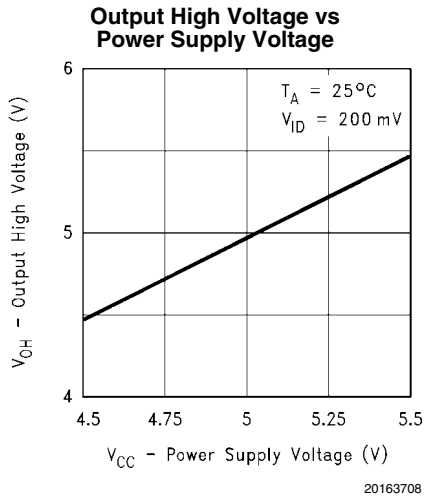
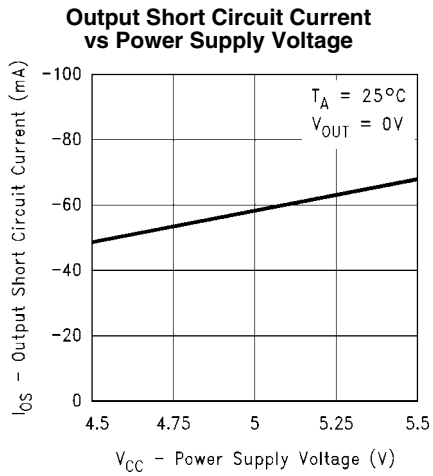


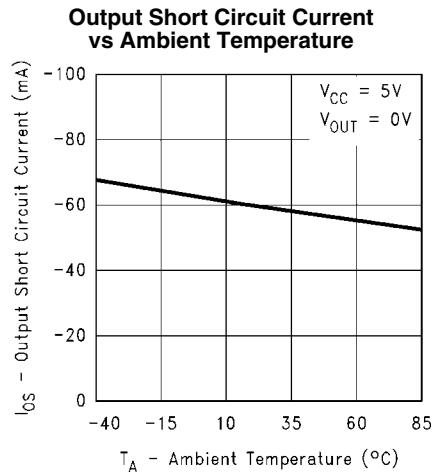
FIGURE 4. Receiver TRI-STATE Delay Waveforms

Typical Performance Characteristics

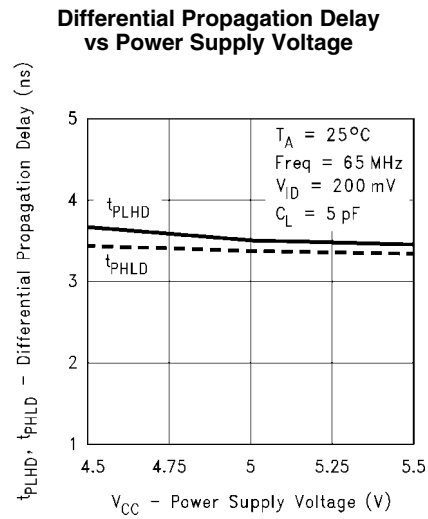




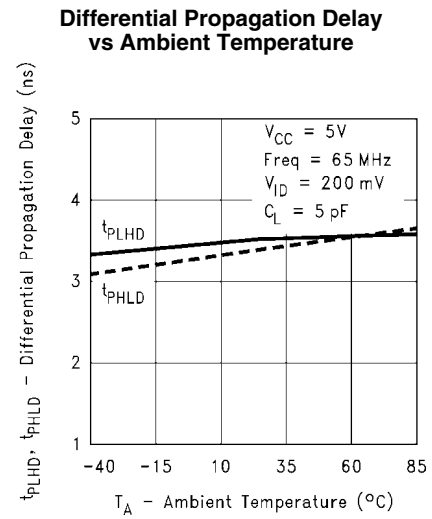
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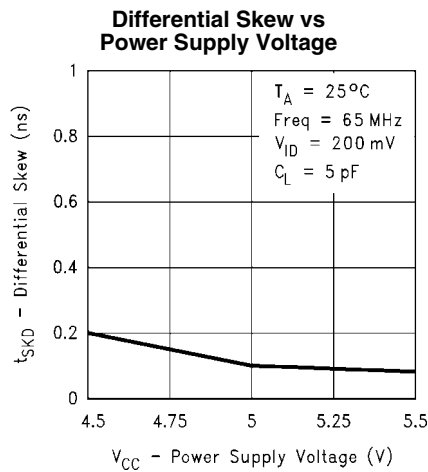
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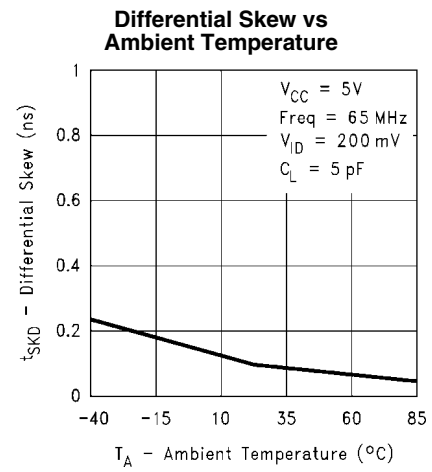
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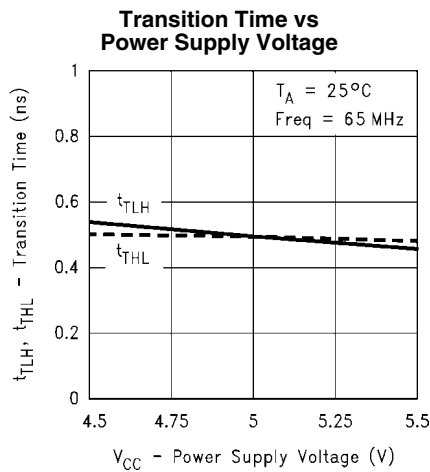
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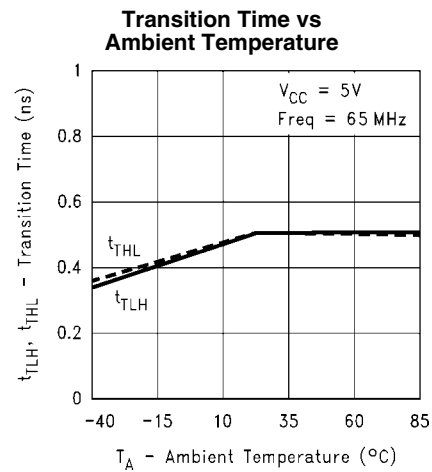
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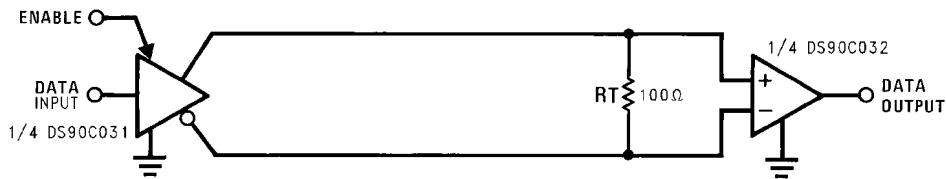


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Typical Application



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FIGURE 5. Point-to-Point Application

Applications Information

LVDS drivers and receivers are intended to be primarily used in an uncomplicated point-to-point configuration as is shown in *Figure 5*. This configuration provides a clean signaling environment for the quick edge rates of the drivers. The receiver is connected to the driver through a balanced media which may be a standard twisted pair cable, a parallel pair cable, or simply PCB traces. Typically the characteristic impedance of the media is in the range of 100Ω. A termination resistor of 100Ω should be selected to match the media, and is located as close to the receiver input pins as possible. The termination resistor converts the current sourced by the driver into a voltage that is detected by the receiver. Other configurations are possible such as a multi-receiver configuration, but the effects of a mid-stream connector(s), cable stub(s), and other impedance discontinuities as well as ground shifting, noise

margin limits, and total termination loading must be taken into account.

The DS90C032 differential line receiver is capable of detecting signals as low as 100 mV, over a ±1V common-mode range centered around +1.2V. This is related to the driver offset voltage which is typically +1.2V. The driven signal is centered around this voltage and may shift ±1V around this center point. The ±1V shifting may be the result of a ground potential difference between the driver's ground reference and the receiver's ground reference, the common-mode effects of coupled noise, or a combination of the two. Both receiver input pins should honor their specified operating input voltage range of 0V to +2.4V (measured from each pin to ground), exceeding these limits may turn on the ESD protection circuitry which will clamp the bus voltages.

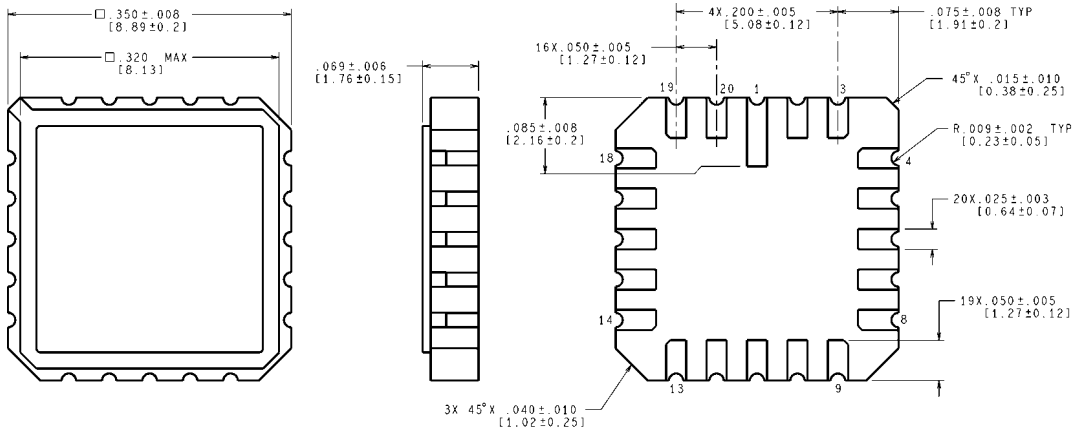
Pin Descriptions

Pin No. (SOIC)	Name	Description
2, 6, 10, 14	R _{I+}	Non-inverting receiver input pin
1, 7, 9, 15	R _{I-}	Inverting receiver input pin
3, 5, 11, 13	R _O	Receiver output pin
4	EN	Active high enable pin, OR-ed with EN*
12	EN*	Active low enable pin, OR-ed with EN
16	V _{CC}	Power supply pin, +5V ± 10%
8	Gnd	Ground pin

Revision History

Released	Revision	Section	Originator	Changes
03/01/06	A	New Release, Corporate format	L. Lytle	1 MDS data sheet converted into Corp. data sheet format. MNDS90C032-X-RH Rev 1B1 will be archived.
10/10/06	B	Applications Information - Pg. 10, Physical Dimensions - Pg. 12	B. Petcher	Deleted Shorted Inputs paragraph - page 10. Updated Physical Dimensions package drawings E20A, W16A to current revision - page 12. Revision A will be Archived.
05/07/07	C	Receiver Table - Pg. 2, Application Information - Pg. 9 & 10	B. Petcher	Deleted Full Fail-safe OPEN/SHORT or terminated - Page 2. & Paragraph RECEIVER FAIL-SAFE and 1, 2, 3 - Page 9 & 10. Revision B will be Archived.

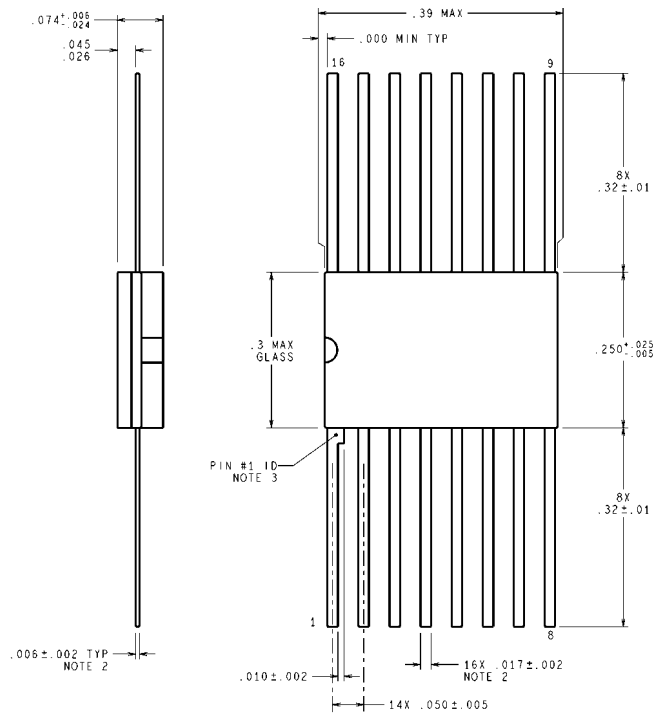
Physical Dimensions inches (millimeters) unless otherwise noted



CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS

E20A (Rev F)

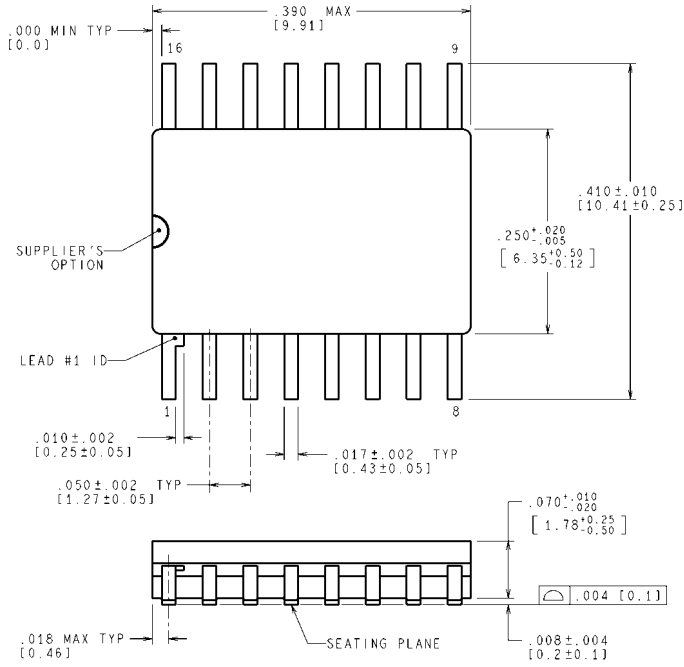
**20-Lead Ceramic Leadless Chip Carrier
NS Package Number E20A**



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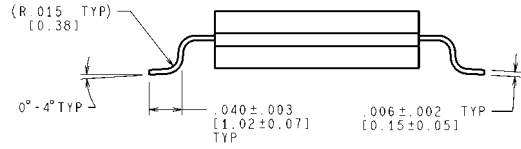
**16-Lead Ceramic Flatpack
NS Package Number W16A**

W16A (Rev T)



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MIL-PRF-38535
CONFIGURATION CONTROL



WG16A (Rev D)

**16-Lead Ceramic SOIC
NS Package Number WG16A**

Notes

DS90C032QML

Notes

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